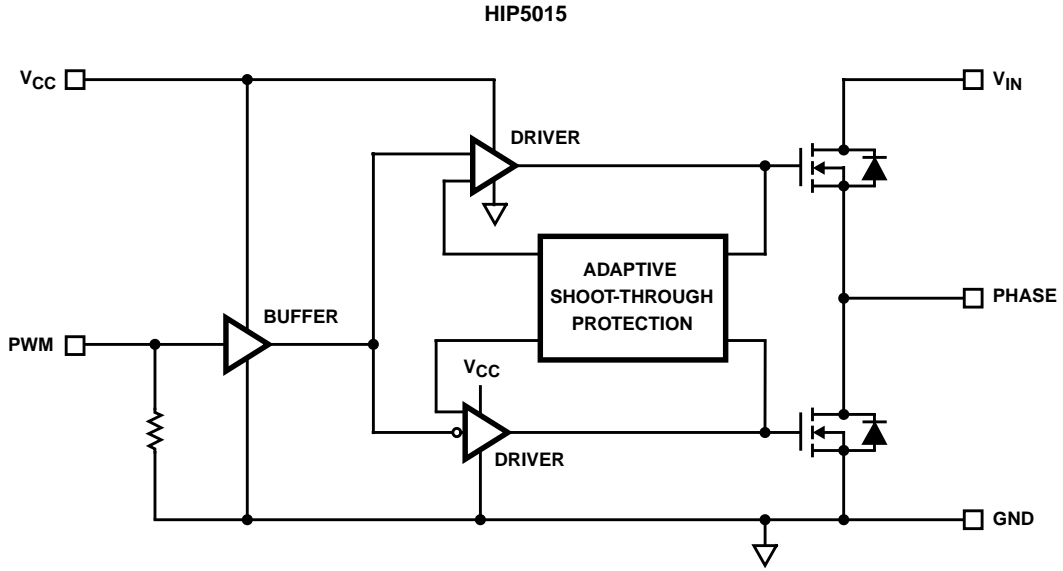
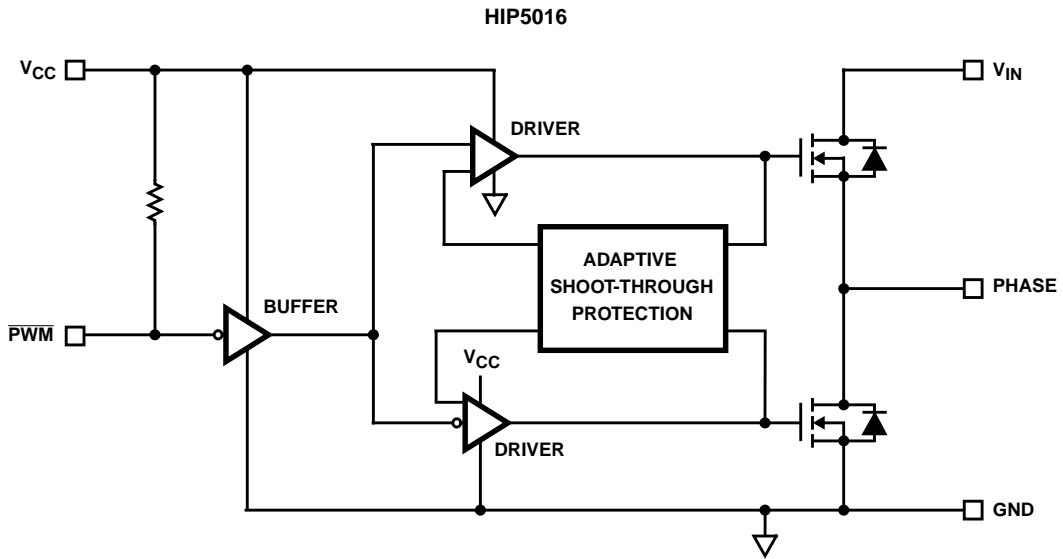




**Non-Inverting SynchroFET Block Diagram**



**Inverting SynchroFET Block Diagram**



# HIP5015, HIP5016

## Absolute Maximum Ratings

Supply Voltage, $V_{CC}$	+16V
Input Voltage $V_{IN}$	+7V
$I_{PHASE}$ , $I_{VIN}$ , $I_{GND}$	7A (Repetitive Peak)
PWM Input	-4V to +16V
ESD Classification	Class 3 (4kV)
Lead Temperature (Soldering 10s) (Lead Tips Only)	300°C
Storage Temperature Range	-65°C to 150°C
Junction Temperature Range	-40°C to 150°C

## Operating Conditions

Supply Voltage, $V_{CC}$	+12V, $\pm 20\%$
Input Voltage $V_{IN}$	0V to 5.5V
Supply Voltage, $V_{CC}$ , minimum for charge-pumped start-up	+4.0V

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the recommended operating conditions of this specification is not implied.

## Thermal Information (Typical)

Package	$\theta_{JC}^{\dagger\dagger}$ (°C/W)	$\theta_{JA}$ (°C/W) <sup>†</sup>				
		0	1	2	3	3 <sup>†††</sup>
SIP (IS)	2	55	30	25	24	18
SIP (IS1)	2	55	-	-	-	-

<sup>†</sup> Versus additional square inches of 1 ounce copper on the printed circuit board.

<sup>††</sup>  $\theta_{JC}$  is typical with an infinite heatsink.

<sup>†††</sup> 200 linear feet per minute of air flow.

$I_{PHASE}$	.5A
$I_{VIN}$	.4A
$I_{GND}$	.3A

## Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	$T_J = 25^\circ\text{C}$			$T_J = -40^\circ\text{C}$ $T_J = +150^\circ\text{C}$		UNITS
			MIN	TYP	MAX	MIN	MAX	
$r_{DS(ON)}$ Upper MOSFET	$R_{DSU}$	$V_{CC} = 12\text{V}$ , $V_{IN} = 5\text{V}$	-	68	78	-	130	m $\Omega$
$r_{DS(ON)}$ Lower MOSFET	$R_{DSL}$	$V_{CC} = 12\text{V}$ , $V_{IN} = 5\text{V}$	-	72	82	-	136	m $\Omega$
$V_{IN}$ Operating Current	$I_{VINO}$	$V_{IN} = 5\text{V}$ , No Load, 500kHz	-	1.8	4	-	5	mA
$V_{IN}$ Quiescent Current	$I_{VIN}$	PWM or $\overline{\text{PWM}} = V_{CC}$ or GND	-	0.1	10	-	100	$\mu\text{A}$
$V_{CC}$ Operating Current	$I_{CCO}$	$V_{CC} = 12\text{V}$ , 500kHz	-	4.3	7	-	9	mA
$V_{CC}$ Quiescent Current (HIP5015)	$I_{CCIH}$	PWM = $V_{CC}$	-	40	-	-	300	$\mu\text{A}$
$V_{CC}$ Quiescent Current (HIP5015)	$I_{CCIL}$	PWM = GND	-	0.1	10	-	100	$\mu\text{A}$
$V_{CC}$ Quiescent Current (HIP5016)	$I_{CCNIH}$	$\overline{\text{PWM}} = V_{CC}$	-	0.1	10	-	100	$\mu\text{A}$
$V_{CC}$ Quiescent Current (HIP5016)	$I_{CCNIL}$	$\overline{\text{PWM}} = \text{GND}$	-	100	-	-	300	$\mu\text{A}$
Low Level PWM Input Voltage	$V_{IL}$		-	1.8	-	1	-	V
High Level PWM Input Voltage	$V_{IH}$		-	2.1	-	-	3	V
PWM Input Voltage Hysteresis	$V_{IHYS}$		-	0.3	-	-	-	V
Input Pulldown Resistance (HIP5015)	$R_{PWM}$		-	220	-	100	400	k $\Omega$
Input Pullup Resistance (HIP5016)	$R_{PWM}$		-	220	-	100	400	k $\Omega$

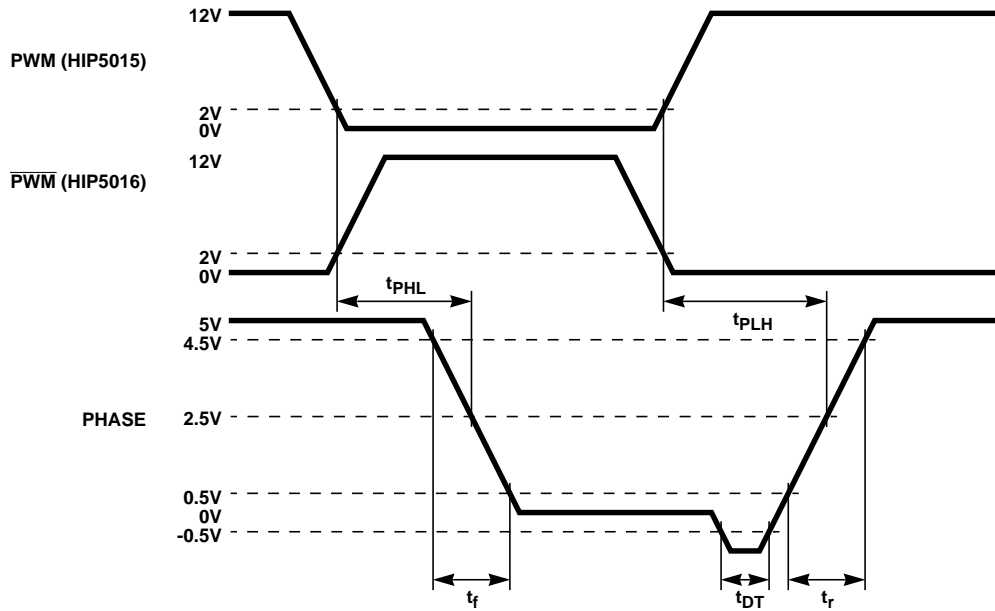
## Switching Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	$T_J = 25^\circ\text{C}$			$T_J = -40^\circ\text{C}$ $T_J = +150^\circ\text{C}$		UNITS
			MIN	TYP	MAX	MIN	MAX	
Upper Device Turn-Off Delay	$t_{PHL}$	$V_{CC} = 12\text{V}$ , $I_{PHASE} = -0.5\text{A}$	-	30	50	-	80	ns
Lower Device Turn-Off Delay	$t_{PLH}$	$V_{CC} = 12\text{V}$ , $I_{PHASE} = +0.5\text{A}$	-	30	50	-	80	ns
Dead Time	$t_{DT}$	$V_{CC} = +12\text{V}$ , $I_{PHASE} = -0.5\text{A}$	-	10	-	-	-	ns
Phase Rise-Time	$t_r$	$V_{CC} = 12\text{V}$ , $I_{PHASE} = -0.5\text{A}$	-	20	-	-	-	ns
Phase Fall-Time	$t_f$	$V_{CC} = 12\text{V}$ , $I_{PHASE} = +0.5\text{A}$	-	20	-	-	-	ns

**Pin Descriptions**

SYMBOL	DESCRIPTION
V <sub>CC</sub>	Positive supply to control logic and gate drivers. De-couple this pin to GND.
V <sub>IN</sub>	FET Switch Input Voltage. De-couple this pin to GND.
PHASE	Output.
PWM (HIP5015) PWM (HIP5016)	Single Ended Control Input. This input connects to the PWM controller output.
GND	System Ground.

**Timing Diagram**



NOTE: I<sub>PHASE</sub> = +0.5A for t<sub>PLH</sub> and t<sub>f</sub>, I<sub>PHASE</sub> = -0.5A for t<sub>PHL</sub>, t<sub>DT</sub>, and t<sub>r</sub>.

**FIGURE 1.**

Typical Performance Curves

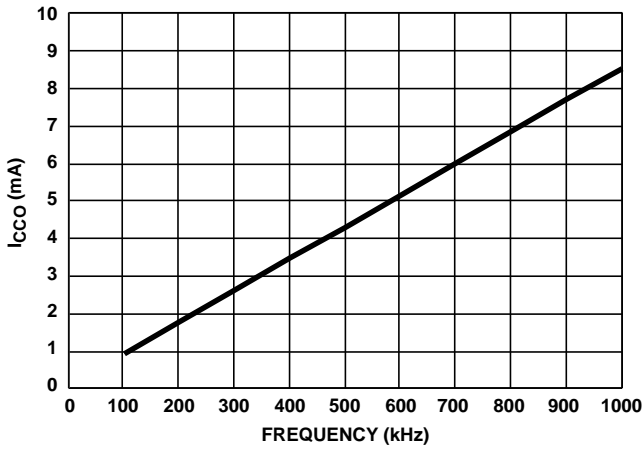


FIGURE 2. I<sub>CCO</sub> vs FREQUENCY

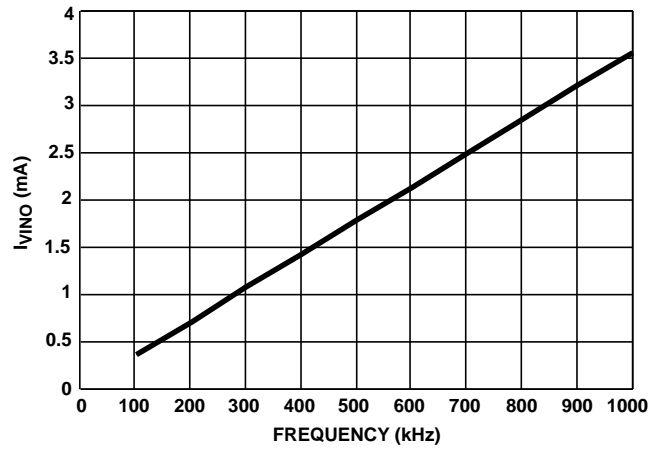


FIGURE 3. I<sub>VINO</sub> vs FREQUENCY

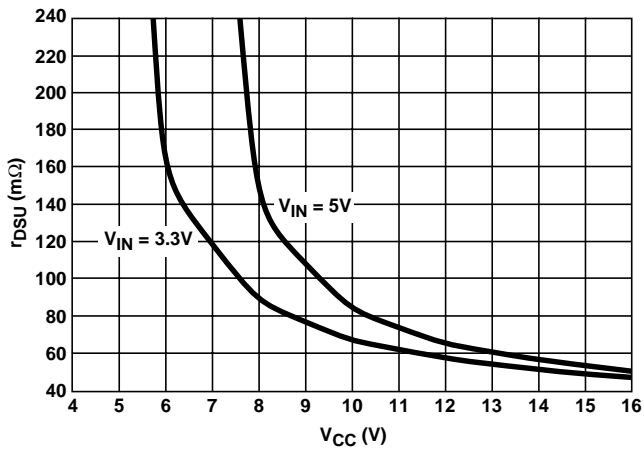


FIGURE 4. R<sub>DSU</sub> vs V<sub>Cc</sub>

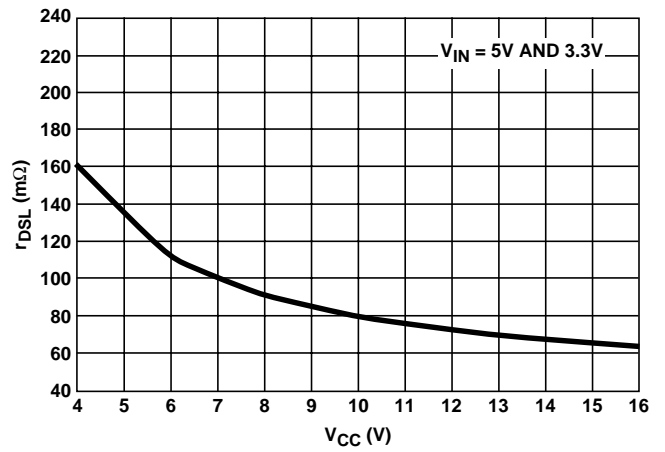


FIGURE 5. R<sub>DSL</sub> vs V<sub>Cc</sub>

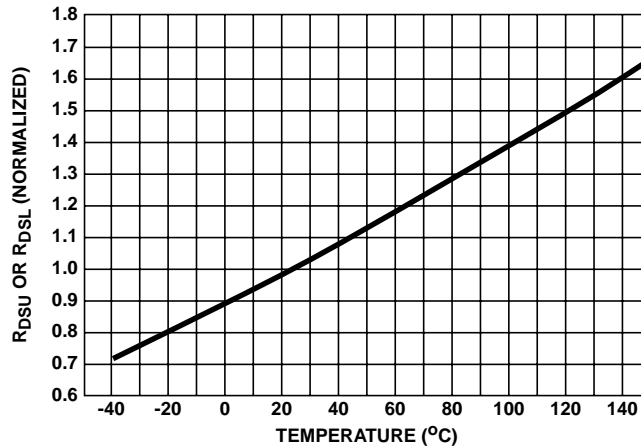


FIGURE 6. R<sub>DSU</sub> OR R<sub>DSL</sub> vs TEMPERATURE

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